

TrenchFET Power MOSFET

ACG: 9H'9@97HF=75@'7<5F57H9F=GH=7G'VæMGíÁ'CA' }|^••Á[c@^| , á•^Á•]^&â-â^â'

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250 A	-			V
Zero gate voltage drain current	I _{BSS}	V _{DS} = -24V, V _{GS} = 0V			-1	A
Gate-source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Drain-source on-resistance (note 1)	R _{DS(on)}	V _{GS} = -10V, I _D = -4.1A		í€	60	m
		V _{GS} = -4.5V, I _D = -3A		îì	87	m
Forward tranconductance (note 1)	g _{FS}	V _{DS} = -5V, I _D = -4A	5.5			S
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 A	-1	ÉÈÈ	-3	V
Diode forward voltage (note 1)	V _{SD}	I _S = -1A, V _{GS} = 0V			-1	V
Dynamic characteristics (note 2)						
Input capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz		700		pF
Output capacitance	C _{oss}			120		pF
Reverse transfer capacitance	C _{rss}			75		pF
Switching Characteristics (note 2)						
Turn-on delay time	t _{d(on)}	V _{GS} = -10V, V _{DS} = -15V, R _L = 3.6 Ω, R _{GEN} = 3 Ω		8.6		ns
Turn-on rise time	t _r			5.0		ns
Turn-off delay time	t _{d(off)}			28.2		ns
Turn-off fall time	t _f			13.5		ns

Notes:

1. Pulse test: Pulse width 300 μs, duty cycle 2%.
2. These parameters have no way to verify.

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